

L Number	Hits	Search Text	DB	Time stamp
-	162	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane or alkoxide) same (single adj crystal or epitax\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/25 17:16
-	97	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane or alkoxide) same (single adj crystal or epitax\$3) same film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/25 17:21
-	27	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) same (single adj crystal or epitax\$3) same film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/26 11:15
-	8	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) same (single adj crystal or epitax\$3) and (atmospheric adj pressure or one adj atm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/25 17:42
-	29	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) same (single adj crystal or epitax\$3) and pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/25 17:48
-	191	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) same (oxygen or "o.sub.2") same pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/25 17:53
-	103	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) same (oxygen or "o.sub.2") same pressure and (438/\$4.cccls. or 117/\$4.cccls)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/26 09:50
-	7	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) and atomic adj layer adj epitax\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/26 11:26
-	18	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) and atomic adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/26 11:31
-	28	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) same (epitax\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/26 11:37
-	7	(tetramethoxysilane or tetraethoxysilane or tetrapropoxy silane or tetrabutoxysilane or (silicon adj alkoxide)) near20 (epitax\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/26 11:39
-	29	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane or (silicon adj alkoxide)) and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/26 11:48
-	52	(normal adj pressure adj cvd ) and (tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) and pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/26 14:41

-	123	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) and (oxide same epitax\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 15:02
-	26	(tetramethoxysilane or tetraethoxysilane or tetrapropoxysilane or tetrabutoxysilane) and (117/\$4.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 15:29
-	253	(silicon adj (dioxide or oxide)) same epitax\$4 and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 15:34
-	113	(silicon adj (dioxide or oxide)) same epitax\$4 and 117/\$4.cccls. and cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 15:36
-	66	(silicon adj (dioxide or oxide)) near20 epitax\$4 and 117/\$4.cccls. and cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 15:50
-	140	(silicon adj (dioxide or oxide)) near40 crystal\$5 and 117/\$4.cccls. and cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 17:30
-	2	ethyl\$1silicate and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 17:37